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October 2013

FQB33N10L

N-Channel QFET® MOSFET

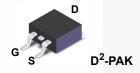
100 V, 33 A, 52 m Ω

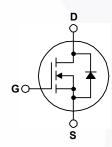
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 33 A, 100 V, $R_{DS(on)}$ = 52 m Ω (Max) @V_{GS} = 10 V, I_D = 16.5 A
- · Low Gate Charge (Typ. 30 nC)
- · Low Crss (Typ. 70 pF)
- 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FQB33N10LTM	Unit	
V _{DSS}	Drain-Source Voltage		100	V	
I _D	Drain Current - Continuous (T _C = 25°C)		33	А	
	- Continuous (T _C = 100°C)		23	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	132	Α	
V _{GSS}	Gate-Source Voltage		± 20	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	430	mJ	
I _{AR}	Avalanche Current	(Note 1)	33	А	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	12.7	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns	
P_{D}	Power Dissipation (T _A = 25°C) *		3.75	W	
	Power Dissipation (T _C = 25°C) - Derate above 25°C		127	W	
			0.85	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
TL	Maximum lead temperature for soldering purposes,		300	°C	
. L	1/8" from case for 5 seconds		300		

Thermal Characteristics

Symbol	Parameter	FQB33N10LTM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	1.18	
В	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (* 1 in² pad of 2 oz copper), Max.	40	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQB33N10L	FQB33N10LTM	D2-PAK	330mm	24mm	800

Flectrical Characteristics

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics		·			
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		0.09		V/°C
I _{DSS} _	Zero Gate Voltage Drain Current	V _{DS} = 100 V, V _{GS} = 0 V			1	μΑ
		V _{DS} = 80 V, T _C = 150°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1.0		2.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 16.5 \text{ A}$ $V_{GS} = 5 \text{ V}, I_D = 16.5 \text{ A}$		0.039 0.043	0.052 0.055	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 30 V, I _D = 16.5 A	\	27		S
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1250	1630	
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		1250	1630	pF
Coss	Output Capacitance			305	400	pF
C _{rss}	Reverse Transfer Capacitance			70	90	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 50 V, I _D = 33 A,		17	45	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		470	950	ns
t _{d(off)}	Turn-Off Delay Time	NG - 20 22		70	150	ns
t _f	Turn-Off Fall Time	(Note 4)	/	120	250	ns
Qg	Total Gate Charge	V _{DS} = 80 V, I _D = 33 A,		30	40	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 5 V	/	4.7		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		16		nC
Drain-S	ource Diode Characteristics ar	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				33	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				132	Α
	- · · · · · · · · · · · · · · · · · · ·		_			

Q_{rr}

 V_{SD}

 t_{rr}

Notes. In Repetitive Rating: Pulse width limited by maximum junction temperature 2. L = 0.59mH, I $_{AS}$ = 33A, V $_{DD}$ = 25V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C 3. I $_{SD}$ \leq 33A, di/dt \leq 300A/ μ s, V $_{DD}$ \leq BV $_{DSS}$, Starting T $_{J}$ = 25°C 4. Essentially independent of operating temperature

Drain-Source Diode Forward Voltage

Reverse Recovery Time

Reverse Recovery Charge

 $V_{GS} = 0 \text{ V, } I_{S} = 33 \text{ A}$

 $V_{GS} = 0 \text{ V}, I_{S} = 33 \text{ A},$

 $dI_F / dt = 100 A/\mu s$

1.5

--

90

0.26

٧

ns

μС

Typical Characteristics

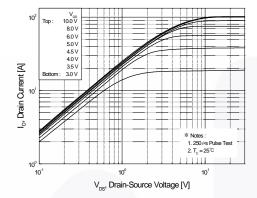


Figure 1. On-Region Characteristics

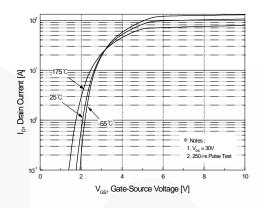


Figure 2. Transfer Characteristics

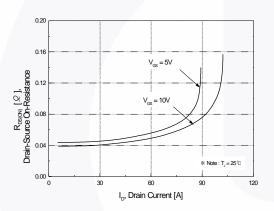


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

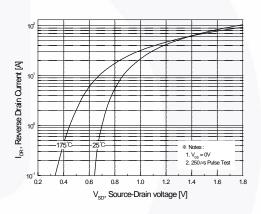


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

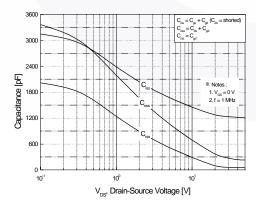


Figure 5. Capacitance Characteristics

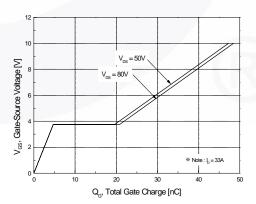


Figure 6. Gate Charge Characteristics

1.2 (Normalized) BAV_{0.88}, (Normalized) # Notes: 1. \(\sigma_{0.98} = 0.0 \) 2. \(\sigma_{0.9} = 2.0 \) 2. \(\sigma_{0.9} = 2.0 \) 4. \(\sigma_{0.9} = 0.0 \) 2. \(\sigma_{0.9} = 0.0 \) 3. \(

Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

 $\mathbf{T}_{_{\!J}}\!,$ Junction Temperature [°C]

150

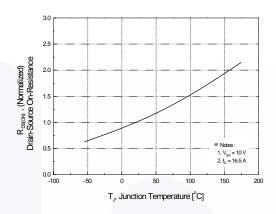


Figure 8. On-Resistance Variation vs. Temperature

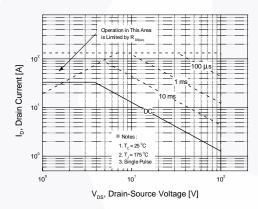


Figure 9. Maximum Safe Operating Area

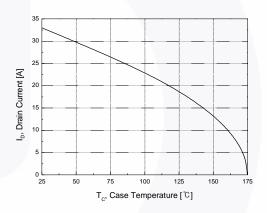


Figure 10. Maximum Drain Current vs. Case Temperature

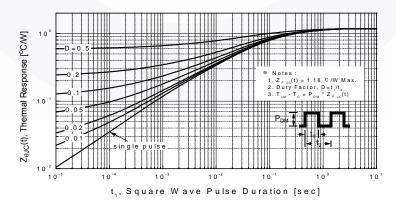


Figure 11. Transient Thermal Response Curve



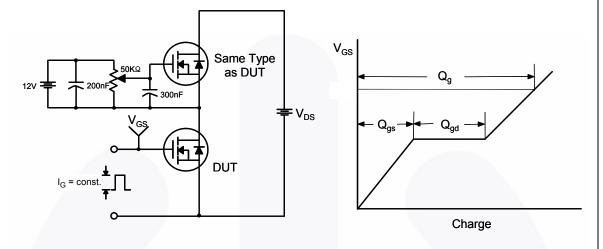


Figure 13. Resistive Switching Test Circuit & Waveforms

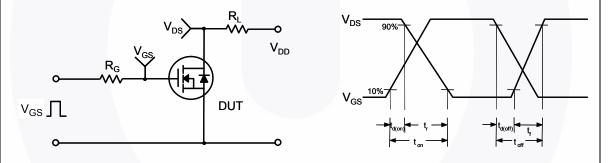
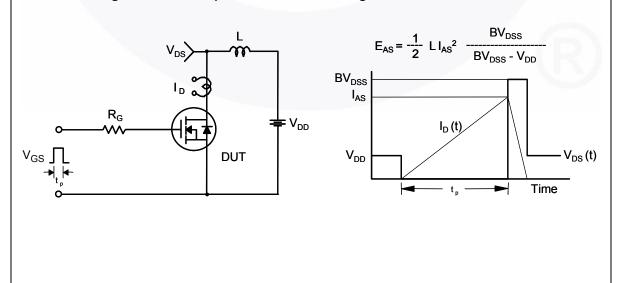
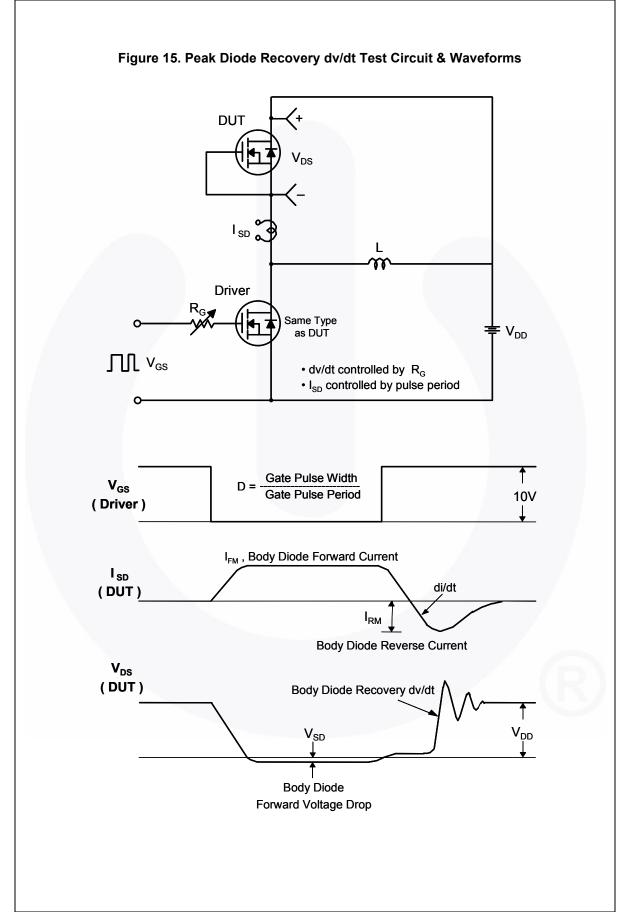


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





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Mechanical Dimensions

TO-263 2L (D²PAK)

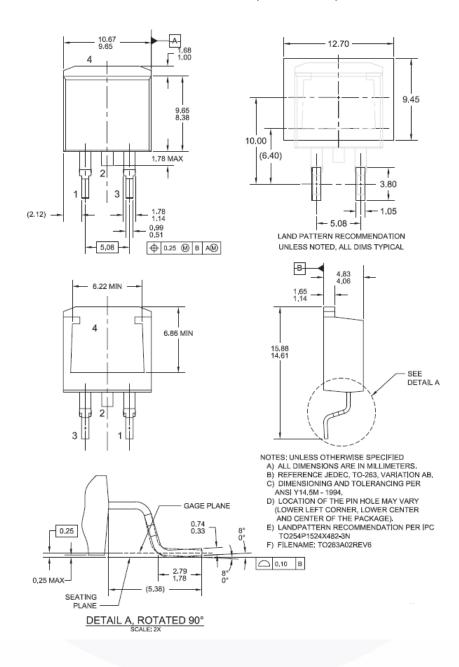


Figure 16. 2LD, TO263, Surface Mount

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Dimension in Millimeters





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